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December 2013

FCH47N60

N-Channel SuperFET® MOSFET

600 V, 47 A, 70 mΩ

Features

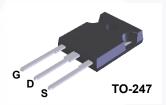
- 650 V @ T_J = 150°C
- Typ. $R_{DS(on)}$ = 58 m Ω
- Ultra Low Gate Charge (Typ. Q_g = 210 nC)
- Low Effective Output Capacitance (Typ. C_{oss(eff.)} = 420 pF)
- · 100% Avalanche Tested
- · RoHS Compliant

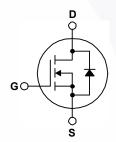
Applications

- · Solar Inverter
- · AC-DC Power Supply

Description

SuperFET® MOSFET is Fairchild Semiconductor's first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low onresistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter	FCH47N60_F133	Unit
V _{DSS}	Drain to Source Voltage		600	V
. \	Drain Current	Continuous (T _C = 25°C)	47	^
ID	Diain Current	Continuous (T _C = 100°C)	29.7	A
I _{DM}	Drain Current	Pulsed (Note 1)	141	Α
V _{GSS}	Gate to Source Voltage		±30	V
E _{AS}	Single Pulsed Avalanche Ener	gy (Note 2)	1800	mJ
I _{AR}	Avalanche Current	(Note 1)	47	Α
E _{AR}	Repetitive Avalanche Energy	(Note 1)	41.7	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns
D	Dower Dissipation	(T _C = 25°C)	417	W
P_{D}	Power Dissipation	Derate Above 25°C	3.33	W/°C
T _J , T _{STG}	Operating and Storage Tempe	rature Range	-55 to +150	°C
TL	Maximum Lead Temperature for 1/8" from Case for 5 Seconds	or Soldering,	300	°C

Thermal Characteristics

Symbol	Parameter	FCH47N60_F133	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	41.7	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCH47N60_F133	FCH47N60	TO-247	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25$ °C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
Design to Occurs Baseledown Veltage	Drain to Source Progledown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}, T_C = 25^{\circ}\text{C}$	600	-	-	V
BV _{DSS} Drain-to-Source Breakdown Volta		$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}, T_C = 150^{\circ}\text{C}$	-	650	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	-	0.6	-	V/°C
BV _{DS}	Drain to Source Avalanche Breakdown Voltage	V _{GS} = 0 V, I _D = 47 A	-	700	-	V
ı	Zoro Cata Voltago Proin Current	V _{DS} = 600 V, V _{GS} = 0 V	-	-	1	^
IDSS	Zero Gate Voltage Drain Current	V _{DS} = 480 V, T _C = 125°C	-	-	10	μΑ
I _{GSS}	Gate-to-Body Leakage Current	V _{GS} = ±30 V, V _{DS} = 0 V	-	-	±100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu A$	3.0	-	5.0	٧
R _{DS(on)}	Static Drain-to-Source On Resistance	V_{GS} = 10 V, I_{D} = 23.5 A	-	0.058	0.070	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 40 \text{ V}, I_{D} = 23.5 \text{ A}$	-	40	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 05.V.V 0.V	-	5900	8000	pF
C _{oss}	Output Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz		3200	4200	pF
C _{rss}	Reverse Transfer Capacitance			250	-	pF
C _{oss}	Output Capacitance	V _{DS} = 480 V, V _{GS} = 0 V, f = 1.0 MHz	-	160	-	pF
C _{oss(eff.)}	Effective Output Capacitance	V _{DS} = 0 V to 400 V, V _{GS} = 0 V	-	420	-	pF

Switching Characteristics

t _{d(on)}	Turn-On Delay		-	185	430	ns
t _r	Turn-On Rise Time	$V_{DD} = 300 \text{ V}, I_D = 47 \text{ A},$	- /	210	450	ns
t _{d(off)}	Turn-Off Delay	$V_{GS} = 10 \text{ V}, R_G = 25 \Omega$		520	1100	ns
t _f	Turn-Off Fall Time	(Note	-	75	160	ns
Q _{g(tot)}	Total Gate Charge at 10 V	V _{DS} = 480 V, I _D = 47 A,	-	210	270	nC
Q_{gs}	Gate to Source Gate Charge	$V_{DS} = 480 \text{ V}, I_{D} = 47 \text{ A},$ $V_{GS} = 10 \text{ V}$	-	38	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(Note	-	110	-	nC

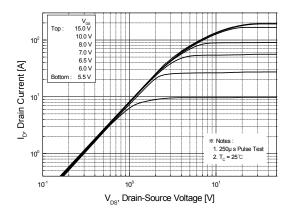
Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain-to-Source Diode Forward Current			-	47	Α
I _{SM}	Maximum Pulsed Drain-to-Source Diode Forward Current			-	141	Α
V_{SD}	Drain-to-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{SD} = 47 \text{ A}$	-	-	1.4	V
t _{rr}	Reverse-Recovery Time	V _{GS} = 0 V, I _{SD} = 47 A, dI _E /dt = 100 A/μs	-	590	-	ns
Q _{rr}	Reverse-Recovery Charge	dI _F /dt = 100 A/μs	_	25	_	μС

Notes:

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. I $_{AS}$ = 18 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 Ω , starting T $_{J}$ = 25°C.
- 3. $I_{SD} \le 48$ A, di/dt ≤ 200 A/ μ s, $V_{DD} \le BV_{DSS}$, starting T_J = 25°C.
- 4. Essentially independent of operating temperature.

Typical Performance Characteristics



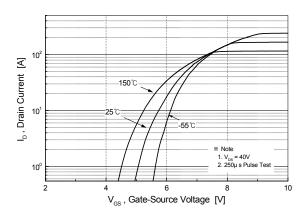


Figure 1. On-Region Characteristics

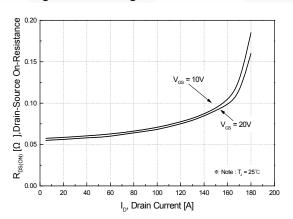


Figure 2. Transfer Characteristics

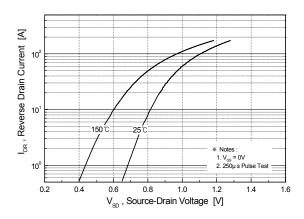


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

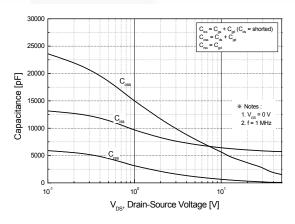


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

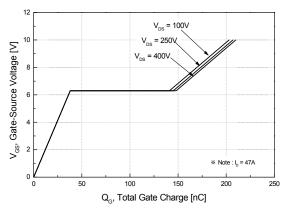
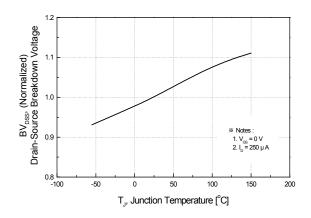


Figure 5. Capacitance Characteristics

Figure 6. Gate Charge Characteristics

Typical Performance Characteristics (Continued)



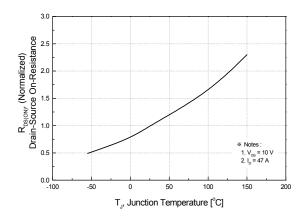
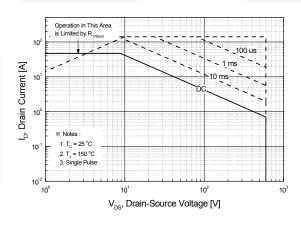


Figure 7. Breakdown Voltage Variation vs. Temperature





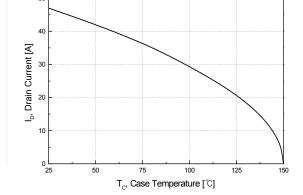


Figure 9. Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

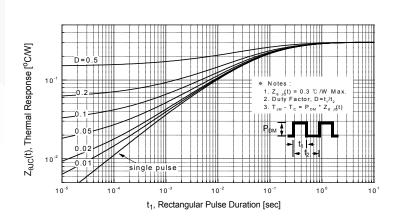


Figure 11. Transient Thermal Response Curve

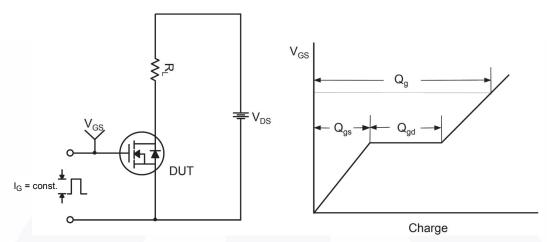


Figure 13. Gate Charge Test Circuit & Waveform

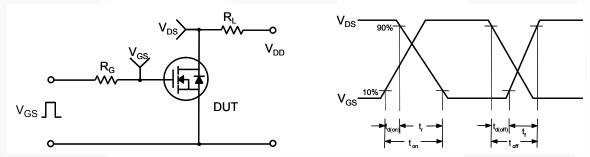


Figure 14. Resistive Switching Test Circuit & Waveforms

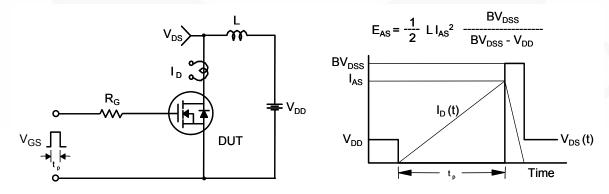


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

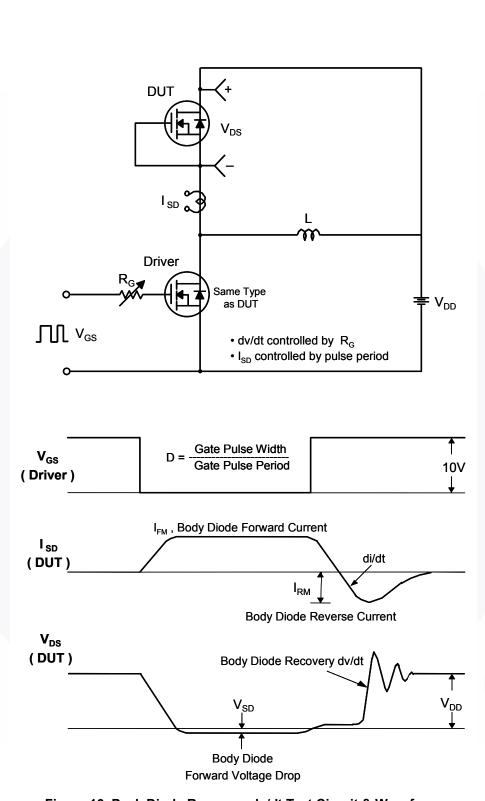
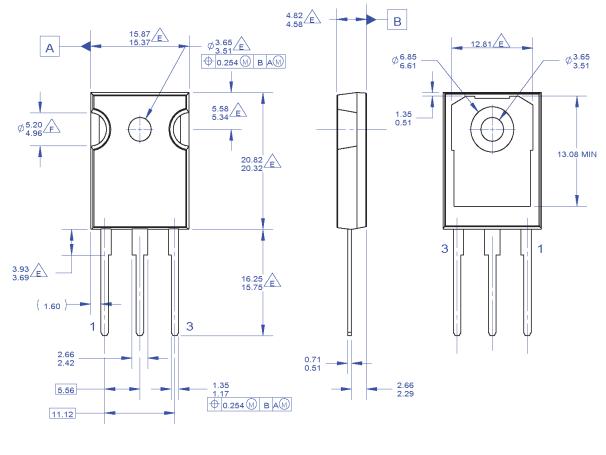


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED

- A. PACKAGE REFERENCE: JEDEC TO-247, ISSUE E, VARIATION AB, DATED JUNE, 2004.
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Figure 17. TO-247, Molded, 3-Lead, Jedec Variation AB

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